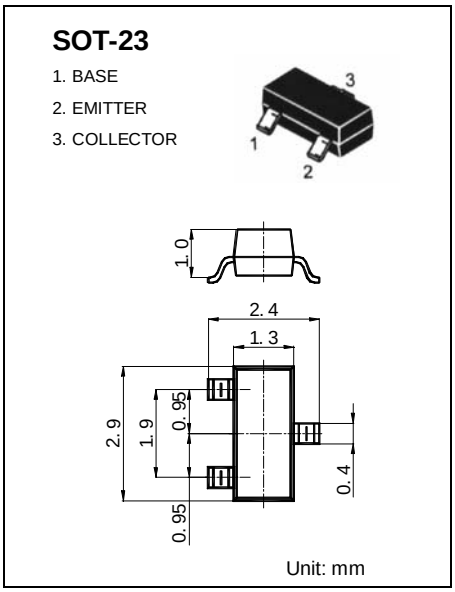
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

BCX19LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.225 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 10μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 10mA, I_B=0	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=20V, I_B=0			0.1	μA
Collector cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC current gain	h_{FE}	V_{CE}=1V, I_C= 100mA	100		600	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500 mA, I_B=50mA			0.62	V
Base-emitter voltage	V_{BE}(on)	I_C=500 mA, V_{CE}=1V			1.2	V

Marking	**U1**